Understanding of disorder for enhancement of superconducting topological gap

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Abstract

Progress in the emergent field of topological superconductivity relies on synthesis of new material combining superconductivity, low density, and spinorbit coupling (SOC). Theory indicates that the interface between a one-dimensional semiconductor with strong SOC and a superconductor hosts Majorana-modes with nontrivial topological properties [1]. We discuss the recent developments in epitaxial growth of AI on InAs nanowires shown to yield a high-quality was superconductor-semiconductor system with uniformly transparent interfaces. We have developed a two-dimensional (2D) surface InAs quantum wells with epitaxial superconducting Aluminum [2], yielding a planar system with exceptional structural and transport characteristics [3]. We based present new qubits on semiconductor weak links dubbed These qubits Gatemons. show great promise on this platform for realization of topological qubits where we unprecedented control over proximity effect in semiconductors using a gate voltage [4]. We discuss the role of disorder and how they could enable potential circuit applications for low power circuits, gate-based topological gubits as well as superconducting gubits for computation [5].

References

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Figures



Figure 1: Planar Josephson Junctions exhibiting signatures of topological phase.